

# MOS FET FKV660S

## 絶対最大定格

(Ta=25°C)

記号	規格値	単位
V <sub>DSS</sub>	60	V
V <sub>GSS</sub>	+20, -10	V
I <sub>D</sub>	±60	A
I <sub>D(pulse)</sub> *	±180	A
P <sub>D</sub>	60 (T <sub>c</sub> =25°C)	W
T <sub>ch</sub>	150	°C
T <sub>stg</sub>	-40~+150	°C

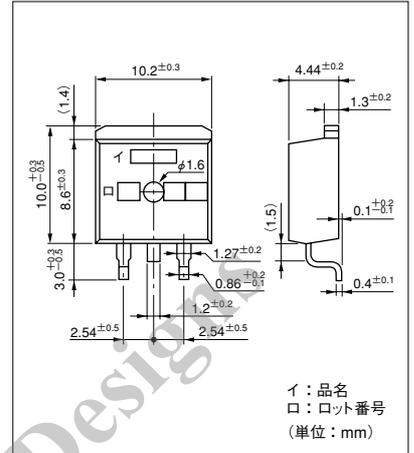
※: P<sub>W</sub> ≤ 100μs, duty ≤ 1%

## 電気的特性

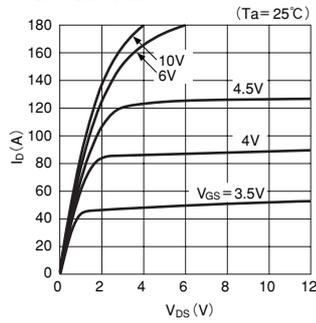
(Ta=25°C)

記号	試験条件	規格値			単位
		min	typ	max	
V <sub>(BR)DSS</sub>	I <sub>D</sub> =100μA, V <sub>GS</sub> =0V	60			V
I <sub>GSS</sub>	V <sub>DS</sub> =+20V			+10	μA
	V <sub>DS</sub> =-10V			-5	
I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			100	μA
V <sub>TH</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =250μA	1.0		2.5	V
R <sub>e(yfs)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =25A	20			S
R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =25A		11	14	mΩ
	V <sub>DS</sub> =10V		2500		pF
	f=1.0MHz		900		pF
C <sub>oss</sub>	V <sub>GS</sub> =0V		150		pF
C <sub>rss</sub>					
t <sub>d(on)</sub>	I <sub>D</sub> =25A		50		ns
t <sub>r</sub>	V <sub>DD</sub> =12V		400		ns
t <sub>d(off)</sub>	R <sub>L</sub> =0.48Ω		400		ns
t <sub>f</sub>	V <sub>GS</sub> =10V		300		ns
V <sub>SD</sub>	I <sub>SD</sub> =50A, V <sub>GS</sub> =0V	1.0		1.5	V

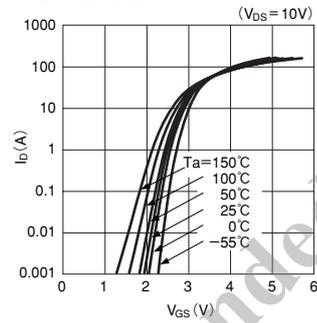
## 外形図 TO220S



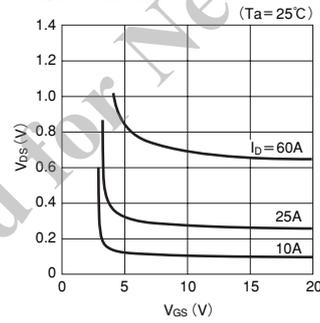
### ■ I<sub>D</sub>-V<sub>DS</sub>特性



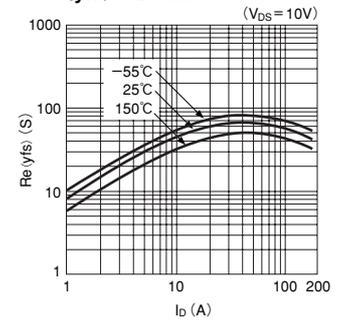
### ■ I<sub>D</sub>-V<sub>GS</sub>特性



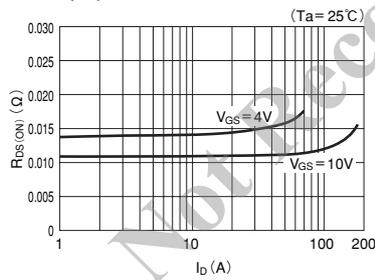
### ■ V<sub>DS</sub>-V<sub>GS</sub>特性(代表例)



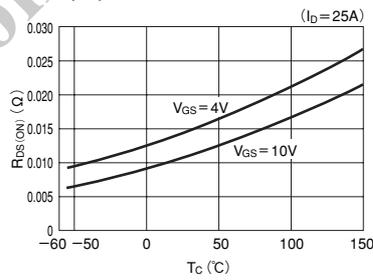
### ■ R<sub>e(yfs)</sub>-I<sub>D</sub>特性



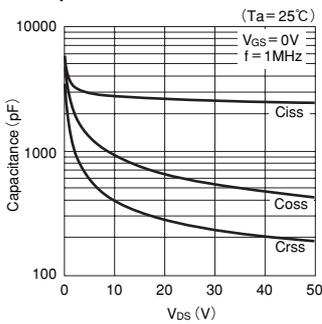
### ■ R<sub>DS(ON)</sub>-I<sub>D</sub>特性



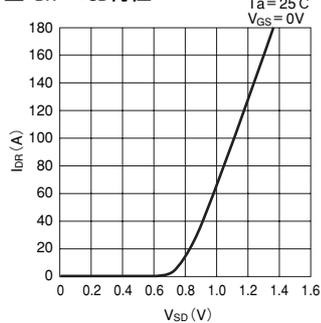
### ■ R<sub>DS(ON)</sub>-T<sub>C</sub>特性



### ■ Capacitance-V<sub>DS</sub>特性



### ■ I<sub>DR</sub>-V<sub>SD</sub>特性



### ■ ASO 曲線(単発パルス)

